



PATENT
0020-4652P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Narihiro MOROSAWA et al. Conf.: 7107
Appl. No.: 09/471,173 Group: 2826
Filed: December 23, 1999 Examiner: K. Quinto
For: INSULATED GATE TRANSISTOR AND PROCESS
FOR FABRICATING THE SAME (To be
Amended)

16/D
3/12/3
Euler

REPLY UNDER 37 C.F.R. § 1.111

Assistant Commissioner for Patents
Washington, DC 20231

March 3, 2003
(Monday)

Sir:

In reply to the Examiner's Office Action dated October 2, 2002, the period for response having been extended two months to March 2, 2003, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE TITLE:

Please amend the title to read: "INSULATED GATE TRANSISTOR HAVING A GATE INSULATOR CONTAINING NITROGEN ATOMS AND FLUORINE ATOMS".

IN THE CLAIMS:

Please amend the following claim:

03/04/2003 JBALINAW 00000147 09471173

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